INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(PTO-1449)

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ATTY. DOCKET NO.	SERIAL NO.
057454-0972	**10/663,674**
APPLICANT: **Hideto HIDAKA**	
FILING DATE: **September 17, 2003**	GROUP: **2824**

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EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Codes (if known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
ap	A1	US	2003/0002333	01/02/2003	Hidaka	
ap	B1	US	6,185,130	02/06/2001	Hollmer et al.	
ap	B2	US	6,856,539	02/15/2005	Hidaka	
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EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes-Number-Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation Yes	Translation No
ap	A2	EP 1 225 591	07/24/2002	Kabushiki Kaisha Toshiba			
ap	A1	DE 101 30 829 w/English abstract	07/18/2002	Mitsubishi Electric Corp.			
ap	A1	DE 102 28 578 w/English abstract	01/16/2003	Mitsubishi Electric Corp.			

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
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EXAMINER	DATE CONSIDERED
Anh Phung	8/31/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

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ATTY. DOCKET NO.	SERIAL NO.
57454-972	**Divisional of Appln. Serial No. 10/135,459**
APPLICANT: **Hideto HIDAKA**	
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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Codes (if known)		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
		Scheuerlein, et al., "A 10ns Read and Write Non-Volatile Memory Array Using A Magnetic Tunnel Junction and FET Switch in Each Cell" ISSCC Digest of Technical Paper, TA 7.2, February 8, 2000, pp. 94-95, 128-129 and 409-410.	
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EXAMINER	DATE CONSIDERED
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